

MOS FIELD EFFECT TRANSISTOR NP100P04PLG

SWITCHING P-CHANNEL POWER MOSFET

DESCRIPTION

The NP100P04PLG is P-channel MOS Field Effect Transistor designed for high current switching applications.

ORDERING INFORMATION <R>

PART NUMBER	LEAD PLATING	PACKING	PACKAGE
NP100P04PLG-E1-AY Note		T 000 -/	TO 000 (MD 057D)
NP100P04PLG-E2-AY Note	Pure Sn (Tin)	Tape 800 p/reel	TO-263 (MP-25ZP)

Note Pb-free (This product does not contain Pb in external electrode.)

FEATURES

• Super low on-state resistance

 $R_{DS(on)1} = 3.7 \text{ m}\Omega \text{ MAX.} \text{ (V}_{GS} = -10 \text{ V}, I_{D} = -50 \text{ A)}$

 $R_{DS(on)2} = 5.1 \text{ m}\Omega \text{ MAX}. \text{ (V}_{GS} = -4.5 \text{ V}, I_{D} = -50 \text{ A})$

- High current rating: I_{D(DC)} = ∓100 A
- · Built-in gate protection diode

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

	· · ·		
Drain to Source Voltage (V _{GS} = 0 V)	VDSS	-40	V
Gate to Source Voltage (V _{DS} = 0 V)	Vgss	∓20	V
Drain Current (DC) (Tc = 25°C)	ID(DC)	∓100	Α
Drain Current (pulse) Note1	D(pulse)	∓300	Α
Total Power Dissipation (Tc = 25°C)	P _{T1}	200	W
Total Power Dissipation (T _A = 25°C)	P _{T2}	1.8	W
Channel Temperature	Tch	175	°C
Storage Temperature	Tstg	-55 to +175	°C
Single Avalanche Current Note2	las	74	Α
Single Avalanche Energy Note2	Eas	550	mJ

Notes 1. PW \leq 10 μ s, Duty Cycle \leq 1%

2. Starting T_{ch} = 25°C, V_{DD} = -30 V, R_G = 25 Ω , V_{GS} = -20 \rightarrow 0 V

THERMAL RESISTANCE

Channel to Case Thermal Resistance 0.75 °C/W $R_{th(ch-C)}$ Channel to Ambient Thermal Resistance 83.3 °C/W Rth(ch-A)

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(TO-263)



ELECTRICAL CHARACTERISTICS (TA = 25°C)

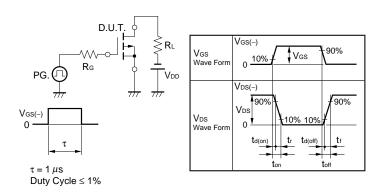
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = -40 V, V _{GS} = 0 V			-10	μΑ
Gate Leakage Current	Igss	V _{GS} = ∓20 V, V _{DS} = 0 V			∓10	μΑ
Gate to Source Threshold Voltage	V _{GS(th)}	V _{DS} = -10 V, I _D = -1 mA	-1.0	-1.6	-2.5	V
Forward Transfer Admittance Note	y fs	V _{DS} = -10 V, I _D = -50 A	43	88		S
Drain to Source On-state Resistance Note	RDS(on)1	V _{GS} = -10 V, I _D = -50 A		2.8	3.7	mΩ
	RDS(on)2	V _{GS} = -4.5 V, I _D = -50 A		3.4	5.1	mΩ
Input Capacitance	Ciss	V _{DS} = -10 V,		15100		pF
Output Capacitance	Coss	V _{GS} = 0 V,		2400		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		1130		pF
Turn-on Delay Time	t _{d(on)}	$V_{DD} = -20 \text{ V}, I_D = -50 \text{ A},$		38		ns
Rise Time	tr	V _{GS} = -10 V,		30		ns
Turn-off Delay Time	t _{d(off)}	R _G = 0 Ω		300		ns
Fall Time	t f			100		ns
Total Gate Charge	Q _G	$V_{DD} = -32 \text{ V},$		320		nC
Gate to Source Charge	Qgs	V _{GS} = -10 V,		37		nC
Gate to Drain Charge	Q _{GD}	I _D = -100 A		85		nC
Body Diode Forward Voltage Note	V _{F(S-D)}	I _F = -100 A, V _{GS} = 0 V		0.91	1.5	V
Reverse Recovery Time	trr	I _F = -100 A, V _{GS} = 0 V,		70		ns
Reverse Recovery Charge	Qrr	di/dt = –100 A/μs		123		nC

Note Pulsed test PW \leq 350 μ s, Duty Cycle \leq 2%

TEST CIRCUIT 1 AVALANCHE CAPABILITY

$PG. \bigcirc PG. \bigcirc PG.$

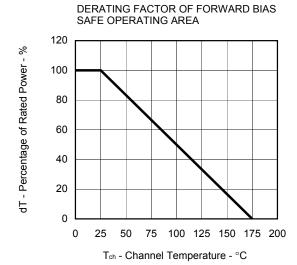
TEST CIRCUIT 2 SWITCHING TIME

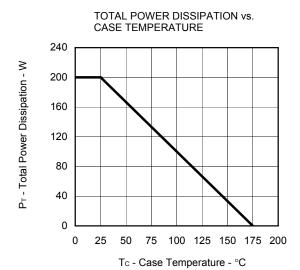


TEST CIRCUIT 3 GATE CHARGE

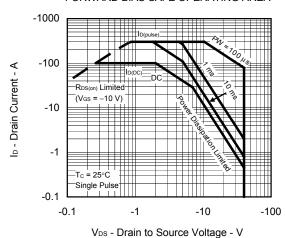
$$\begin{array}{c|c} D.U.T. & \\ \hline \\ IG = -2 \text{ mA} \\ \hline \\ PG. & \\ \hline \\ \end{array} \begin{array}{c} RL \\ \hline \\ VDD \\ \hline \end{array}$$

TYPICAL CHARACTERISTICS (TA = 25°C)

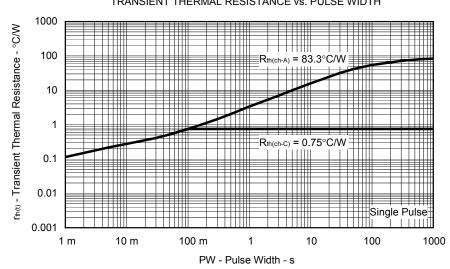




FORWARD BIAS SAFE OPERATING AREA

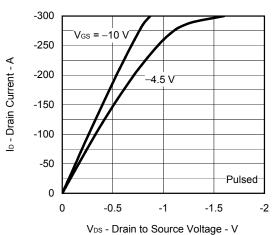


TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

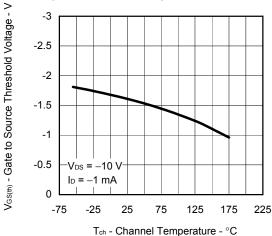


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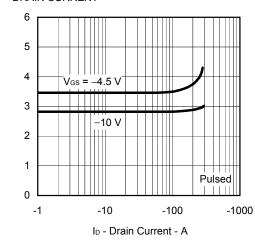




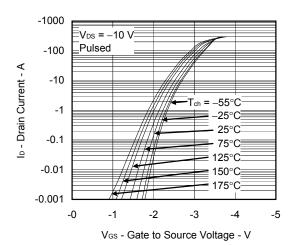
GATE TO SOURCE THRESHOLD VOLTAGE vs. CHANNEL TEMPERATURE



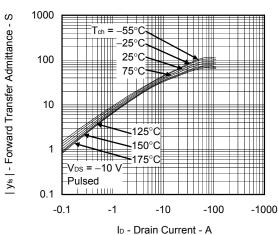
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



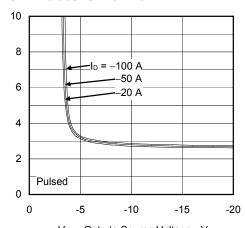
FORWARD TRANSFER CHARACTERISTICS



FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



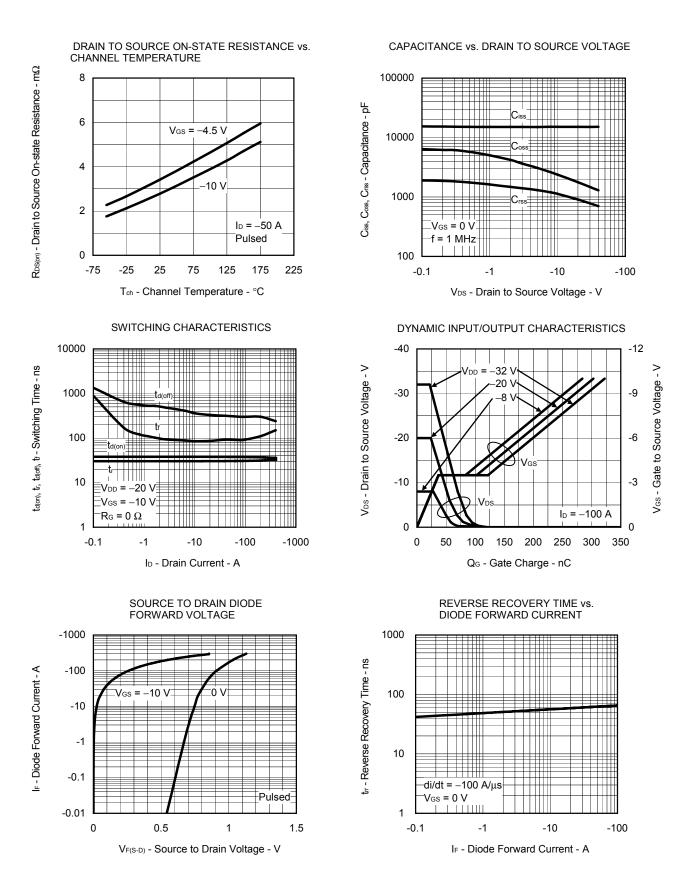
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



V_{GS} - Gate to Source Voltage - V

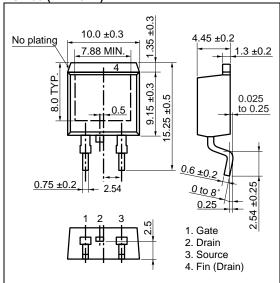
R_{DS(o1)} - Drain to Source On-state Resistance - mΩ

RDS(on) - Drain to Source On-state Resistance - mΩ

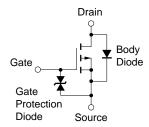


PACKAGE DRAWING (Unit: mm)

TO-263 (MP-25ZP)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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